IN THE SPECIFICATION:

Please amend the specification as follows:

Please amend the paragraph beginning on page 1, line 11, as follows.

-- 2. DESCRIPTION OF THE RELATED ART --.

Please amend paragraph [0004], as follows.

-- [0005] In the projection exposure apparatus for exposing the large substrate for use in the liquid crystal display panel or the like to form the circuit pattern thereon, the provision of a large-diameter projection optical system capable of exposing a large substrate to form a whole desired mask pattern thereon at [[a]] one time presents problems in the footprint, weight, stability, and cost of the apparatus. Thus, a certain type of projection optical system forms part of a mask pattern image in a slit-like shape, wherein a mask and a substrate are moved for scanning with respect to the projection system. This eliminates the need for the large-diameter projection optical system to allow the small apparatus to achieve exposure in a large region. --

Please amend paragraph [0020], as follows.

-- [0020] According to a fourth aspect of the present invention, a method of projection exposure and a method of manufacturing an exposed member, ~~comprise~~ include the steps of a first step of preparing a mask including plural columns of a mask pattern for

repeated exposure to a member to form columns of an exposure pattern thereon, and a second step of alternately performing light projection from the mask onto the member through light irradiation to the mask and step movement of the member for moving the member by a movement amount equal to n times a pitch of the columns of the exposure pattern (where n is a natural number smaller than the number of the columns of the mask pattern). At the second step, a light shielding region is formed to prevent light projection onto the member from some of the plural of columns of the mask pattern, and the light shielding region is moved in a step manner by a movement amount corresponding to a pitch equal to n columns of the mask pattern in a light projection region on the member in association with step driving of the member in an early phase and a later phase of the repeated exposure. --

Please amend paragraph [0032], as follows.

-- [0032] Figs. 10(A) and 10(B) are explanatory ~~view~~ views of an exposure mask for use in a liquid crystal substrate exposure apparatus which is Embodiment 2 of the present invention; --

Please amend paragraph [0057], as follows.

-- [0057] Since a full-scale image of the mask pattern is projected onto the substrate 3 in the exposure apparatus of Embodiment 1, the pixel mask pattern columns ~~has~~ have a pitch P identical to a pitch (an arrangement pitch) of the pixel pattern columns to be

exposed on the substrate 3. In the following, the pitch of the pixel pattern columns exposed on the substrate 3 is also represented by P. --

Please amend paragraph [0061], as follows.

-- [0061] Embodiment 1 is particularly useful when the mask 4, which has the pixel mask pattern 4a (and the driver mask pattern 4c) for repeatedly exposing the discontinuous cyclic pattern and the gate line mask pattern 4b for exposing the continuous pattern is used as described above. Thus, the description is continued with such a case taken as an example. However, Embodiment 1 is also useful when a mask which has no mask pattern for exposing a continuous pattern is used. --

Please amend paragraph [0062], as follows.

-- [0062] Next, a description is made ~~for~~ of an exposure operation of the liquid crystal substrate exposure apparatus of Embodiment 1 when the aforementioned mask 4 is used. In the exposure operation in Embodiment 1, the substrate 3 is repeatedly exposed to form the respective patterns thereon by alternately performing projection of exposure light onto the substrate 3 from the respective mask patterns 4a to 4c by irradiation of illumination light from the illumination system 7 to the mask 4 and step movement of the substrate 3 resulting from step driving of the substrate stage 5 while the mask 4 is fixed. --

Please amend paragraph [0068], as follows.

-- [0068] For example, when the mask 4 has the five columns (a=5) and setting is made such that five projection operations of exposure light are performed to provide a required amount of exposure light (b=5), 5xP/5=P (n=1<a=5), ~~and thus~~ the step movement amount of the substrate 3 is equal to the pitch P of the pixel pattern columns exposed on the substrate 3. Alternatively, if the mask has six pixel pattern columns (a=6) and setting is made such that three projection operations of exposure light are performed to provide a required amount of exposure light (b=3), 6xP/3=2xP (n=2<a=6), ~~and thus~~ the step movement amount of the substrate 3 is equal to two pitches P of the pixel pattern columns formed on the substrate 3. --

Please amend paragraph [0070], as follows.

-- [0070] When the substrate 3 is moved in a step manner and exposure is performed at each ~~stop~~ step position in this manner, the pixels are formed on the substrate 3 through b projection operations. Specifically, when an amount of exposure light required in proper exposure for the pixels is defined as A (mW), an amount of exposure light in one shot may be A/b (mW). Thus, a proper amount of exposure light can be provided finally even when the light source 56 emits a small amount of light. --

Please amend paragraph [0073], as follows.

-- [0073] Fig. 3(A) shows the substrate 3 in an early phase in a series of exposure steps. First, a ~~1'st~~ first shot is performed as the first projection (shot) of exposure light.

This results in exposure of the substrate 3 to expose five pixel pattern columns 1L′ to 5L′ thereon. An amount of exposure light in this shot corresponds to A/b (mW) described above and does not reach the required amount of exposure light.--

Please amend paragraph [0074], as follows.

-- [0074] Next, the substrate 3 is moved in a step manner to the left in Fig. 3(A) for one pitch of the pixel pattern columns and stopped, and then a ~~2-d~~ second shot is performed. In the ~~2-d~~ second shot, superposed exposure is performed for the second to fifth pixel pattern columns 2L to 5L from the left of the five pixel pattern columns exposed in the previous ~~1-t~~ first shot. In the ~~2-d~~ second shot, a new pixel pattern column is also exposed on the right of the rightmost pixel pattern column 5L exposed in the ~~1-t~~ first shot.

Please amend paragraph [0075], as follows.

-- [0075] Next, the substrate 3 is moved in a step manner for one pitch of the pixel pattern columns and stopped, and then a ~~3'rd~~ third shot is performed. This achieves third exposures for the third to fifth pixel pattern columns 3L′ to 5L′ from the left of the five pixel pattern columns exposed in the ~~1'st~~ first shot. In the ~~3'rd~~ third shot, a new pixel pattern column is also exposed on the right of the pixel pattern column newly exposed in the ~~2'nd~~ second shot. --

Please amend paragraph [0076], as follows.

-- [0076] Thereafter, each time the substrate 3 is moved in a step manner for one pitch of the pixel pattern columns, a subsequent shot is performed (as a fourth, a fifth, a sixth shot or the like). As a result, an amount of exposure light in the fifth column or later from the leftmost pixel pattern column 1L exposed in the ~~1t~~ first shot reaches the proper amount of exposure light which corresponds to the amount of exposure light for five shots, that is, A (mW). --

Please amend paragraph [0077], as follows.

-- [0077] Five exposures (shots) are not performed in the first to fourth pixel pattern columns 1L′ to 4L′ from the leftmost column exposed in the ~~1'st~~ first shot in the early phase of the exposure process. If certain measures are not taken, the proper amount of exposure light is not provided for such pixel pattern columns. --

Please amend paragraph [0080], as follows.

[0080] Fig. 5(A) schematically shows the relationship between the exposure region limited by the light shielding blade 9a and the pixel pattern columns actually exposed on the substrate 3 in the early phase of the exposure process. In Fig. 5(A), an upper section shows the pixel mask pattern on the fixed mask 4, while a lower section shows the pixel pattern exposed on the substrate 3 which is moved in a step manner to the left in Fig. 5(A).--

Please amend paragraph [0081], as follows.

-- [0081] In the upper section, hatched blocks show a region in which the exposure light from the mask 4 toward the projection lens 2 is shielded by the light shielding blade 9a. In the lower section, each block is divided by a dotted line into an upper subblock and a lower subblock, in which the upper subblock shows a pixel pattern column exposed in the current shot, while the lower subblock shows one or plural pixel pattern columns exposed in the previous shot. --

Please amend paragraph [0082], as follows.

-- [0082] Before the ~~1'st~~ first shot is performed, the light shielding blade 9a is moved to a position (a light shielding initial position) where it shields exposure light from the pixel mask pattern columns 1L to 4L and causes exposure light from the pixel mask pattern column 5L to be incident on the projection lens 2. Consequently, in the ~~1t~~ first shot, the pixel pattern columns 1L to 4L corresponding to the pixel mask pattern columns 1L to 4L are not exposed, and only the pixel pattern column 5L corresponding to the pixel mask pattern column 5L is exposed. --

Please amend paragraph [0083], as follows.

-- [0083] Thereafter, each time the substrate 3 is moved in a step manner, the light shielding blade 9a is moved to a position where the light shielding blade 9a shields exposure light from the pixel mask pattern columns 1L to 3L and allows exposure only for

the pixel pattern columns 4L and 5L (in the ~~2-d~~ second shot), to a position where it shields exposure light from the pixel mask pattern columns 1L and 2L and allows exposure only for the pixel pattern columns 3L to 5L (in the ~~3-d~~ third shot), and to a position where it shields exposure light from the pixel mask pattern column 1L and allows exposure only for the pixel pattern columns 2L to 5L (in the ~~4-h~~ fourth shot), sequentially. --

Please amend paragraph [0084], as follows.

-- [0084] In other words, the light shielding blade 9a is moved in a step manner in a direction identical to the step movement direction of the substrate 3 (see the solid line arrow in Fig. 1) in synchronization with the step movement thereof by the movement amount for eliminating the shielding of the exposure light from one pixel mask pattern column (that is, the movement amount for allowing the light projection region on the substrate 3 to change by one (n) pixel mask pattern column, further in other words, the movement amount corresponding to a pitch equal to one (n) column of the pixel mask pattern in the light projection region on the substrate 3). In the ~~5-h~~ fifth shot or later (in the step movement of the substrate 3 after the ~~4-h~~ fourth shot or later), the light shielding blade 9 is retracted to the non-shield position until a later stage of the exposure process, later described. Thus, in the ~~5-h~~ fifth shot or later, the pixel pattern columns 1L to 5L corresponding to all the pixel mask pattern columns 1L to 5L are exposed. --

Please amend paragraph [0085], as follows.

-- [0085] With this operation, it is possible to actually start exposure of the substrate 3 at the position of the pixel pattern column 5L′ corresponding to the pixel mask pattern column 5L exposed in the ~~1'st~~ first shot. Before the ~~1t~~ first shot, the initial position of the substrate 3 is set such that exposure light from the pixel mask pattern column 5L is projected onto the leftmost exposure start position in the pixel pattern exposure region in Fig. 3(A) and Fig. 5(A) (the position where the pixel pattern column 1L is located in Fig. 3(A)), thereby allowing exposure of the pixel pattern columns with the proper amount of exposure light from the exposure start position in the pixel pattern exposure region. --

Please amend paragraph [0090], as follows.

-- [0090] In the later stage of the exposure process, the light shielding blade 9b is retracted to the non-shielding position until an ~~m-4'th~~ m-fourth shot is performed. With the step movement of the substrate 3 after the ~~m-4'th~~ m-fourth shot, the light shielding blade 9b is moved in a step manner to a position where it shields exposure light from the pixel mask pattern column 5L and causes only exposure light from the pixel mask pattern columns 1L to 4L to be incident on the projection lens 2. Thus, in the next ~~m-3 h~~ m-third shot, only the pixel pattern columns 1L to 4L corresponding to the pixel mask pattern columns 1L to 4L are exposed. --

Please amend paragraph [0091], as follows.

-- [0091] Thereafter, each time the substrate 3 is moved in a step manner, the light shielding blade 9b is moved to a position where the light shielding blade 9b shields exposure light from the pixel mask pattern columns 4L and 5L and allows exposure only for the pixel pattern columns 1L to 3L (in an ~~m-2-h~~ m-second shot), to a position where it shields exposure light from the pixel mask pattern columns 3L to 5L and allows exposure only for the pixel pattern columns 1L and 2L (in an ~~m-1-h~~ m-first shot), and to a position where it shields exposure light from the pixel mask pattern columns 2L to 5L and allows exposure only for the pixel pattern column 1L (in the m-th shot), sequentially. --

Please amend paragraph [0101], as follows.

-- [0101] Fig. 7 is a flow chart of operation of the control circuit 8a in the series of exposure steps. ~~Description~~ A description is hereinafter made ~~for~~ of the operation flow chart in conjunction with Fig. 1. --

Please amend paragraph [0104], as follows.

-- [0104] Then, at step S3, the control circuit 8a determines whether or not the shot at step S2 is the ~~5-h~~ fifth shot or later based on the shot count. If the shot does not reach the ~~5-h~~ fifth shot, the flow proceeds to step S4, and the control circuit 8a moves the substrate 3 and the light shielding blade 9a in a step manner as described in Fig. 5(A). Then, the flow returns to step S2 to again perform a shot (exposure). --

Please amend paragraph [0105], as follows.

[0105] On the other hand, if it is determined at step S3 that the shot at step S2 is the ~~5'th~~ fifth shot or later, the flow proceeds to step S5, and the control circuit 8a determines whether or not the shot at step S2 is the ~~m-4 h~~ m-fourth shot or later. It should be noted that m represents the total number of exposures (the number of shots) required for exposing the substrate 3 to form all the circuit patterns thereon with the mask 4, and is previously set through input by a user or the like. --

Please amend paragraph [0106], as follows.

[0106] If it is determined at step S5 that the shot does not reach the ~~m-4'th~~ m-fourth shot, the flow proceeds to step S6 and the control circuit 8a moves only the substrate 3 in a step manner. Then, the flow returns to step S2 to again perform a shot (exposure). --

Please amend paragraph [0107], as follows.

-- [0107] If it is determined at step S5 that the shot at step S2 is the ~~m-4'th~~ m-fourth shot or later, the flow proceeds to step S7 and the control circuit 8a determines whether or not the shot at step S2 is the last shot (the m-th shot). If it is determined that the shot is not the last shot (the m-th shot), the flow proceeds to step S8, and the control circuit 8a moves the substrate 3 and the light shielding blade 9b in a step manner as described in Fig. 5(B). --

Please amend paragraph [0117], as follows.

-- [0117] In the following description, ~~component~~ components identical to those of the liquid crystal substrate exposure apparatus in Embodiment 1 are designated with the same reference numerals as those in Embodiment 1. --

Please amend paragraph [0120], as follows.

-- [0120] Fig. 11 shows the substrate 3, which is subjected to exposure for the tab pattern subsequent to exposure for the pixel pattern in a later stage of the exposure process. In Embodiment 2, each of an ~~m-5-h~~ m-fifth shot to an m-th shot corresponding to the later stage of the exposure process is performed after the mask 14 and the substrate 3 are synchronously moved in a step manner in the same direction, to expose the tab pattern together with the pixel pattern (and the gate line pattern and the driver pattern). --

Please amend paragraph [0121], as follows.

-- [0121] Although not shown in Fig. 11, in an early phase of the exposure process, each of a ~~2'nd~~ second shot after a ~~1'st~~ fifth shot to a ~~6'th~~ sixth shot is performed after the mask 14 and the substrate 3 are synchronously moved in a step manner in the same direction, to expose the tab pattern and the pixel pattern (and the gate line pattern and the driver pattern). --

Please amend paragraph [0124], as follows.

-- [0124] In the mask 14, the first tab mask pattern 14d has the width of 2xP as ~~describe~~ described above. Of the first tab mask pattern 14d, a portion having the width P away from the pixel mask pattern column 1L (on the outer side) is referred to as T1a, while a portion having the width P close to the pixel mask pattern column 1L (on the inner side) is referred to as T1b. The second tab mask pattern 14d' also has the width of 2xP. Of the second tab mask pattern 14d', a portion having the width P closer to the pixel mask pattern column 5L (on the inner side) is referred to as T2a, while a portion having the width P away from the pixel mask pattern column 5L (on the outer side) is referred to as T2b. --

Please amend paragraph [0128], as follows.

-- [0128] Then, a ~~1'st~~ first shot (exposure) is performed. In the ~~1'st~~ first shot, the substrate 3 is exposed to form a pattern T1a' corresponding to the outer portion T1a of the first tab mask pattern 14d thereon. --

Please amend paragraph [0130], as follows.

-- [0130] Then, a ~~2'nd~~ second shot is performed. In the ~~2'nd~~ second shot after the mask 14 is moved in a step manner in synchronization with the substrate 3, a pattern T1a' corresponding to the outer portion T1a of the first tab mask pattern 14d is formed through superposed exposure on the pattern T1a' exposed in the ~~1'st~~ first shot, and a pattern T1b'

corresponding to the inner portion T1b of the first tab mask pattern 14d is exposed on the right of the pattern T1a'. --

Please amend paragraph [0131], as follows.

-- [0131] Next, the substrate 3 and the mask 14 are moved in a step manner in the same direction, and then a ~~3'rd~~ third shot is performed. In the ~~3'rd~~ third shot, a pattern T1a corresponding to the outer portion T1a of the first tab mask pattern 14d is formed through superposed exposure on the pattern T1a exposed in the ~~1'st~~ first and ~~2'nd~~ second shots, and a pattern T1b corresponding to the inner portion T1b of the first tab mask pattern 14d is exposed through superposed exposure on the pattern T1b formed in the ~~2'nd~~ second shot. On the right of the pattern T1b, a pixel pattern column 1L corresponding to the pixel mask pattern column 1L is newly exposed. When each pixel pattern column is exposed, a portion of the gate line pattern and a portion of the driver pattern present in the exposure region are also exposed simultaneously with the corresponding pixel mask pattern column in the illumination region. --

Please amend paragraph [0132], as follows.

-- [0132] Thereafter, the step movement of the substrate 3 and the mask 14 and the exposure are repeated similarly until a ~~5'th~~ fifth shot. When the outer portion T1a of the first tab mask pattern 14d reaches the leftmost portion of the exposure region, five exposures achieved by superposed exposure are completed for the pattern T1a

corresponding to the outer portion T1a of the first tab mask pattern 14d. At this point, four exposures achieved by superposed exposure have been performed on the pattern T1b corresponding to the inner portion T1b of the first tab mask pattern 14d, three exposures achieved by superposed exposure have been performed on the pixel pattern column $1L_a$, two exposures achieved by superposed exposure have been performed on the pixel pattern column 2L′, and one exposure has been performed on the pixel pattern column 3L′. --

Please amend paragraph [0133], as follows.

-- [0133] In addition, each of a ~~6'th~~ sixth shot and a ~~7'th~~ seventh shot is performed after the step movement of the substrate 3 and the mask 14. In the ~~6'th~~ sixth and ~~7'th~~ seventh shots, since the outer portion T1a of the first tab mask pattern 14d lies outside the illumination region (the exposure region), the pattern T1a is not subjected to superposed exposure more than five times. The pattern T1b on which the fifth exposure is performed in the sixth shot, is not subjected to exposure in the ~~7'th~~ seventh shot since the inner portion T1b of the first tab mask pattern 14d lies outside the illumination region. --

Please amend paragraph [0134], as follows.

-- [0134] At the time when the ~~7'th~~ seventh shot is completed, the pixel mask pattern columns 1L to 5L are present in the illumination region on the mask 14. --

Please amend paragraph [0135], as follows.

-- [0135] After the ~~7'th~~ seventh shot is completed, the mask 14 is stopped (fixed), and only the substrate 3 is moved in a step manner as before to continue exposure. Thus, the images of the pixel mask pattern columns 1L to 4L (1L to 4L are formed through superposed exposure on the previously exposed pixel pattern columns, and the image of a pixel mask pattern mask column 5L (5L is newly exposed in the rightmost portion of the exposure region. It should be noted that, after the mask 14 is stopped, the previously exposed pixel pattern column is overlaid by the image of a pixel mask pattern column different from the pixel mask pattern column corresponding to that previously exposed pixel pattern column through superposed exposure, but no problem occurs since all the pixel mask pattern columns have the same shape. --

Please amend paragraph [0136], as follows.

-- [0136] Next, a description is made ~~for~~ of the later stage of the exposure process with reference to Fig. 13. At the time when an ~~m-6'th~~ m-sixth shot is completed after only the substrate 3 is moved in a step manner, the substrate 3 has pixel pattern columns formed thereon which have been subjected to exposures five times, four times, three times, and ~~twice~~ twice, from the left of the exposure region, and a pixel pattern column which has been subjected to exposure once. --

Please amend paragraph [0137], as follows.

-- [0137] Then, the step movement of the mask 14 in synchronization with the substrate 3 is again started as in the early phase. This results in the pixel mask pattern columns 2L to 5L and the inner portion T2a of the second tab mask pattern 14d′ present in the illumination region on the mask 14. When the ~~m=5'th~~ m-fifth shot is performed in this state, the substrate 3 is exposed to form pixel pattern columns 2L to 5L superposed on the previously formed pixel pattern columns 2L to 5L and a pattern T2a′ corresponding to the inner portion T2a of the second tab mask pattern 14d′. --

Please amend paragraph [0138], as follows.

-- [0138] After the ~~m=5'th~~ m-fifth shot, the substrate 3 and the mask 14 are again moved synchronously in a step manner in the same direction and an ~~m=4'th~~ m-fourth shot is performed. The substrate 3 is exposed to form pixel pattern columns 3L to 5L and a pattern T2a superposed on the previously formed pixel pattern columns 3L to 5L and the pattern T2a respectively, and a pattern T2b corresponding to the outer portion T2b of the second tab mask pattern 14′. --

Please amend paragraph [0139], as follows.

-- [0139] Thereafter, the substrate 3 and the mask 14 are moved in a step manner and then each shot is performed until the last m'th shot as in the early phase. When an ~~m=2'nd~~ m-second shot is performed, five exposures achieved by superimposed exposure for the last pixel pattern column (5L are completed. Then, five exposures achieved by

superposed exposure for the tab patterns T2a and T2b corresponding to the second tab mask patterns 14d′ (T2a and Tb2) are completed. In this manner, a proper amount of exposure light can be provided for all the patterns exposed on the substrate 3. --

Please amend paragraph [0140], as follows.

-- [0140] As described above, the substrate 3 is exposed to form all the pixel pattern (a discontinuous cyclic pattern), the driver ~~pattern~~ patterns (a discontinuous cyclic pattern), the gate line pattern (a continuous pattern), and the tab pattern (the single pattern) thereon with the proper amount of exposure light by using the mask 14 only through one series of exposure steps. --

Please amend paragraph [0145], as follows.

-- [0145] Fig. 15 is a flow chart of operation of a control circuit 8a in the aforementioned series of the exposure steps. ~~Description~~ A description is hereinafter made for the operation flow chat in conjunction with Fig. 1. --

Please amend paragraph [0148], as follows.

-- [0148] Then, at step S13, the control circuit 8a determines whether or not the shot at step S12 is the ~~7'th~~ seventh shot or later based on the shot count. If the shot does not reach the ~~7'th~~ seventh shot, the flow proceeds to step S14 and the control circuit 8a

synchronously moves the substrate 3 and the mask 14 in a step manner. Then, the flow returns to step S12 to again perform a shot (exposure). --

Please amend paragraph [0149], as follows.

-- [0149] On the other hand, if it is determined at step S13 that the shot at step S12 is the ~~7'th~~ seventh shot or later, the flow proceeds to step S15, and the control circuit 8a determines whether or not the shot at step S12 is the ~~m-6'th~~ m-sixth shot or later. If it is determined at step S15 that the shot does not reach the ~~m-6'th~~ m-sixth shot, the flow proceeds to step S16 and the control circuit 8a moves only the substrate 3 in a step manner and stops the mask 14. Then, the flow returns to step S12 to again perform a shot (exposure). --

Please amend paragraph [0150], as follows.

-- [0150] On the other hand, if it is determined at step S15 that the shot at step S12 is the ~~m-6'th~~ m-sixth or later, the flow proceeds to step S17 and the control circuit 8a determines whether or not the shot at step S12 is the last shot (the m-th shot). It should be noted that m represents the total number of exposures (the number of shots) required for exposing the substrate 3 to form all the circuit patterns thereon with the mask 14, and is previously set through input by a user or the like. --

Please amend paragraph [0154], as follows.

-- [0154] In addition, according to Embodiment 2, it is possible to perform the exposure for the discontinuous cyclic patterns (the pixel pattern and the driver pattern), the exposure for the continuous pattern (the gate line pattern), and the exposure for the single pattern (the tab pattern) ~~one~~ in the series of the exposure steps. --

Please amend paragraph [0158], as follows.

-- [0158] Specifically, prior to the ~~1'st~~ first shot in the early phase shown in Fig. 12, the light shielding blade 9a is moved to a position where it shields exposure light through a region between the outer portion T1a of the first tab mask pattern 14d and the left end of the exposure region. The light shielding blade 9a is moved in a step manner after the end of each of the ~~2'nd~~ second to ~~4'th~~ fourth shots to prevent leakage of exposure light from that region. The step movement amount of the light shielding blade 9a corresponds to the step movement amount of the mask 14 and is equal to an amount for changing the projection region on the substrate 3 by n columns (n is equal to 1 in Embodiment 2) of the mask pattern (that is, a movement amount corresponding to a pitch equal to one (n) column of the pixel mask pattern in the projection region on the substrate 3). --

Please amend paragraph [0159], as follows.

-- [0159] In addition, for each of the ~~m-4'th~~ m-fourth shot to ~~m-1'st~~ m-first shot shown in Fig. ~~13~~ 13, in the later stage, the light shielding blade 9b is moved in a step

manner by the amount identical to the aforementioned amount to a position where it shields exposure light through a region between the outer portion T2b of the second tab mask pattern 14d′ and the right end of the exposure region to prevent leakage of exposure light from that region. --

Please amend paragraph [0162], as follows.

-- [0162] (Embodiment 3)

Next, a description is made ~~for~~ of a method of manufacturing a liquid crystal display panel (a semiconductor device) by using the projection exposure apparatus described in each of Embodiments 1 and 2. --

Please amend paragraph [0165], as follows.

-- [0165] At step S104, the exposure process described in Embodiments 1 and 2 is performed. Thus, the method of manufacturing a glass substrate according to Embodiment 3 includes the steps of preparing a mask (steps S101 to S102) and the exposure step (step S104) using the mask and shown in Embodiments 1 and 2. The array manufacture step at step S104 is ~~lager~~ later described in detail. --

Please amend paragraph [0173], as follows.

-- [0173] (Embodiment 4)

In the following, an example of the mask is shown which can be used in the liquid crystal substrate exposure apparatuses described in ~~embodiments~~ Embodiments 1 and 2.

Please amend paragraph [0174], as follows.

-- [0174] Fig. 18(A) shows a mask 24 serving as Embodiment 4. The mask 24 corresponds to the mask 14 described in Fig. ~~10 (A)~~ 10(A) of Embodiment 2 from which the driver pattern 14c is removed. Specifically, the mask 24 has a pixel mask pattern 24a consisting of pattern elements of five columns, a gate line mask pattern 24b, and a tab mask pattern 24d which is formed on both sides of the arranged columns (in a left-right direction in Fig. 18(A)) of the pixel mask pattern 24a. Fig. 18(B) is an enlarged view of a portion B in Fig. 18(A). --

Please amend paragraph [0180], as follows.

-- [0180] In addition, the substrate 3 is exposed while it is moved in a step manner to form a (longitudinal) gate line pattern along each pixel pattern column by using another ~~mask, not shown~~ mask (not shown) (for example, a mask having five gate line mask pattern columns), as in the exposure with the mask 4 in Embodiment 1. --

Please amend paragraph [0185], as follows.

-- [0185] Embodiments 1 to 5 have been described as an exposure technique preferable for use especially in the liquid crystal display panel substrate. However, the

present invention is used not only for the liquid crystal display panel, but also as an exposure technique for use in manufacturing various types of semiconductor devices, a thin film magnetic head, and an image-pickup device (such as a CCD, or a CMOS sensor), and as an exposure technique for transferring a circuit pattern to a glass substrate or a silicon wafer in order to manufacture a reticle or a mask. --

Please amend paragraph [0189], as follows.

-- [0189] The use of the mask including the first mask pattern for exposing the member to form the discontinuous pattern thereon and the second mask pattern for exposing the member to form the continuous pattern thereon allows simultaneous exposure for the discontinuous pattern and the continuous pattern. In addition, the step movement of the member ensures the continuity of the continuous pattern exposed on the member. Consequently, the repeated exposure for the discontinuous pattern and the exposure for the continuous pattern can be performed ~~unseparatedly~~ without separation as the single exposure process (one series of the exposure steps). --

Please amend paragraph [0191], as follows.

-- [0191] While preferred embodiments have been described, it is to be understood that ~~modification~~ modifications and ~~variation~~ variations of the present invention may be made without departing from scope of the following claims. --